

## Refine Search

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Database:

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**IBM Technical Disclosure Bulletins**

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### Search History

DATE: Friday, June 24, 2005    [Printable Copy](#)    [Create Case](#)

<u>Set</u> <u>Name</u> <u>Query</u> side by side	<u>Hit</u> <u>Count</u>	<u>Set</u> <u>Name</u> result set
DB=TDBD; PLUR=YES; OP=OR		
<u>L35</u> L34	0	<u>L35</u>
DB=DWPI; PLUR=YES; OP=OR		
<u>L34</u> L33	0	<u>L34</u>
DB=JPAB; PLUR=YES; OP=OR		
<u>L33</u> L32	0	<u>L33</u>
DB=EPAB; PLUR=YES; OP=OR		
<u>L32</u> L31	0	<u>L32</u>
DB=USOC; PLUR=YES; OP=OR		
<u>L31</u> L30	0	<u>L31</u>
DB=PGPB; PLUR=YES; OP=OR		
<u>L30</u> L29	0	<u>L30</u>
DB=USPT; PLUR=YES; OP=OR		
(("gate wiring nad the mask" or "gate electrode and the mask" or "gate		

<u>L29</u>	wiring and the resist" or "gate electrode and the resist") near3 mask) near5 (dource or drain or impurity)	0	<u>L29</u>
<u>L28</u>	L24 and ((source or drain or impurity) near10 (gate near2 mask) near3 mask)	9	<u>L28</u>
<u>L27</u>	L24 and ((source or drain or impurity) near6 (gate near4 mask) near4 mask)	20	<u>L27</u>
<u>L26</u>	L24 and ((source or drain or impurity) near10 (gate near4 mask) near6 mask)	22	<u>L26</u>
<u>L25</u>	L24 and (impurity same (gate near6 mask) same mask)	21	<u>L25</u>
<u>L24</u>	L21 and (resist same (gate near10 (tungston or W)))	33	<u>L24</u>
<u>L23</u>	L2 and ("gate wiring" same resist)	0	<u>L23</u>
<u>L22</u>	L21 and (gate near10 (tungston or W))	447	<u>L22</u>
<u>L21</u>	"active layer"	16236	<u>L21</u>
<u>L20</u>	"vernier pattern"	107	<u>L20</u>
<u>L19</u>	6476333	2	<u>L19</u>
<u>L18</u>	6476333	2	<u>L18</u>
<u>L17</u>	l15 same "external contacts"	87	<u>L17</u>
<u>L16</u>	L15 same 'external contacts'	87	<u>L16</u>
<u>L15</u>	((silicon or mica or alumina or quartz or sapphire or SiC) near7 (substrate or carrier)) same contacts	26868	<u>L15</u>
<u>L14</u>	((silicon or mica or alumina or quartz or sapphire or SiC) near7 (substrate or carrier)) same coctacts	0	<u>L14</u>
<u>L13</u>	L1 and ((silicon or mica or alumina or quartz or sapphire or SiC) near7 (substrate or carrier))	2	<u>L13</u>
<u>L12</u>	L11 and (different near5 (spacing or pitch))	10	<u>L12</u>
<u>L11</u>	L10 and ((upper near5 contacts) near10 ((carrier or substrate) near7 "lower surface"))	287	<u>L11</u>
<u>L10</u>	L4 near6 ((carrier or substrate) near10 "lower surface")	1128	<u>L10</u>
<u>L9</u>	L8 and (different near5 (spacing or pitch))	60	<u>L9</u>
<u>L8</u>	L7 and ((upper near surface) near7 (upper near5 contacts))	4287	<u>L8</u>
<u>L7</u>	L4 near6 "lower surface"	13231	<u>L7</u>
<u>L6</u>	L5 and (different near5 (spacing or pitch))	602	<u>L6</u>
<u>L5</u>	L4 and (upper near5 contacts)	46804	<u>L5</u>
<u>L4</u>	lower near6 contacts	107910	<u>L4</u>
<u>L3</u>	"lower pattern of contacts"	0	<u>L3</u>
<u>L2</u>	6841812	1	<u>L2</u>
<u>L1</u>	epitax\$5. and 6551865	2	<u>L1</u>

END OF SEARCH HISTORY